ECN3064 is monolithic IC integrating 6 IGBTs.

It can be applied to DC brushless motors and Induction motors.

### Functions

- \* Integrated charge pump circuit
- \* Free Wheeling Diodes are integrated
- \* Overcurrent Protection circuit is integrated

### Features

- \* PWM control of upper and bottom arm IGBTs are possible by controlling outer Microproc essor
- \* 6 Logic inputs are compatible with 5V CMOS or LSTTL outputs
- \* Upper and Bottom arm IGBTs can operate in 20kHz chopping frequency
- \* For converted AC200 to 230 V power supplies

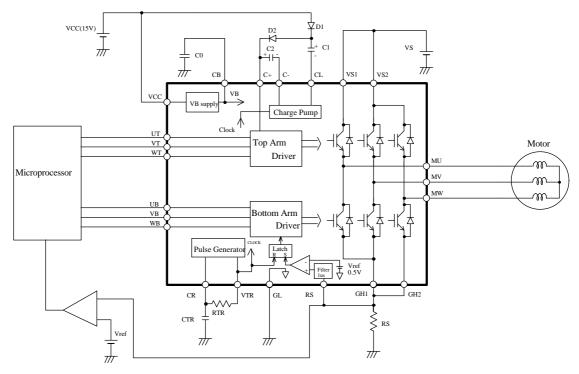


Fig.1 Block Diagram

1. General

(1) Type ECN3064SP, ECN3064SPV,ECN3064SPR

(2) Application 3-Phase DC Brushless Motor and Induction Motor

(3) Structure Monolithic IC

(4) Package SP-23TA, SP-23TB, SP-23TR

2. Maximum Allowable Ratings (Ta=25 °C)

No.	Items	Symbols	Terminal	Ratings	Unit	Condition
1	Output Device	VSM	VS1,VS2	500	V	
	Breakdown Voltage		MU,MV,MW			
2	Supply Voltage	VCC	VCC	18	V	
3	Input Voltage	VIN	UT,VT,WT,	-0.5~ VB+0.5	V	
			UB,VB,WB			
4	Output Current	IMDC	MU,MV,MW	0.7	A	
5	Peak Output Current	IMP	MU,MV,MW	1.5	A	Note 1
6	Output Current in Start	IOM	MU,MV,MW	1.5	A	Note 1
	Up and Accelerating					
7	Operating Junction	Tjop		-20 ~ +125	°C	Note 2
	Temperature					
8	Storage Temperature	Tstg		-40 ~ +150	°C	

Note 1. Please note that aculmulated duty of a period exceeding 0.7A has to be less than 5% of total current flowing period.

Note 2. Thermal Resistance

Rj-c = 4 °C /W

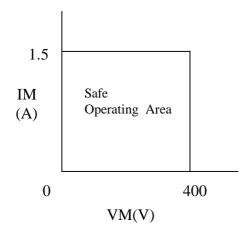
 $Rj-a = 40 \, ^{\circ}C / W$ 

### 3. Recommended Operating Conditions

No.	Items	Symbols	Terminal	MIN	TYP	MAX	Unit	Condition
1	Supply Voltage	VS	VS1,VS2	50	325	400	V	
2		VCC	VCC	13.5	15	16.5	V	

Note 1. Recommended Safe Operating Area(SOA)

It is recommended that this IC is used within the SOA as shown below where IM and VM are the current and the voltage at the terminal of motor wiring at the change of phase (turn off).



4. Electrical Characteristics (Ta=25 °C)

Unless otherwise specified, VCC=15V, VS=325V

Suffix T; Top arm B; Bottom arm

No.	Items	Symbols	Terminal	MIN	TYP	MAX	Unit	Condition
1	Standby Current	IS	VS1,VS2	-	0.5	1.5	mA	UT,VT,WT,UB,VB,
2		ICC	VCC	-	10	20	mA	WB=0V
3	Output device FVD	VFT	MU,MV,	-	2.2	3.0	V	I=0.35A
			MW					
4		VFB	MU,MV,	-	2.2	3.0	V	I=0.35A
			MW					
5	Turn On	TdONT	MU,MV,	-	1.0	2.0	μs	
			MW					
6	Delay Time	TdONB	MU,MV,	-	1.0	2.0	μs	I=0.35A
	<b>—</b> • • • • • • • • • • • • • • • • • • •		MW		1.0			
7	Turn Off	TdOFFT	MU,MV,	-	1.0	2.0	μs	Resistive Load
0	Dalam Time	TAOEED	MW		1.0	2.0		-
8	Delay Time	TdOFFB	MU,MV, MW	-	1.0	2.0	μs	
9	Diode FVD	VFDT	MU,MV,		2.2	2.8	V	I=0.35A
9	Diode FVD	VFDI	MW	-	2.2	2.0	V	1-0.55A
10		VFDB	MU,MV,	_	2.4	3.0	V	-
10		VIDD	MW	_	2.4	5.0	•	
11	Input Voltage	VIH	UT,VT,W	3.5	-	-	V	
	1		T,					
12		VIL	UB,VB,W	-	-	1.5	V	
			В					
13	Input Current	IIH	UT,VT,W	-	-	100	μΑ	Input=5V Note 1
			T,					Pull Down Resistance
			UB,VB,W					
			В					
14	VB Output Voltage	VB	CB	6.8	7.5	8.2	V	
15	VB Output Current	IB	CB	25	-	-	mA	deltaVLoad=0.1V
16	Reference Voltage	Vref	RS	0.45	0.5	0.55	V	
	for Overcurrent							
17	LVSD Output Voltage	LVSDON	VCC,MU,	10.0	11.5	12.9	V	Note.2
18	LVSD recover Voltage	LVSDOFF	MV,MW	10.1	12.0	13.0	V	
19	LVSD reset hysterisis	Vrh		0.1	0.5	0.9	V	

Note 1. Pull Down Resistance are typically 200  $k\Omega.$ 

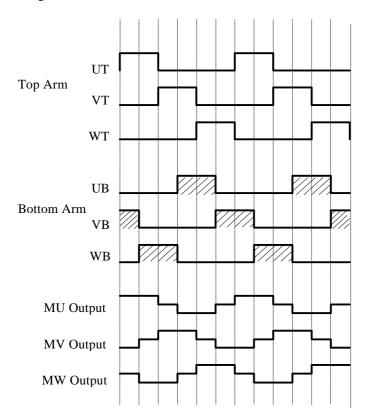
Note 2. LVSD: Low Voltage Shut Down

#### 5. Function

#### 5.1 Truth Table

Terminal	Input	Output	
UT,VT,WT,	L	OFF	
UB,VB,WB	Н	ON	
UT,UB	UT&UB=H	OFF	
VT,VB	VT&VB=H	OFF	
WT,WB	WT&WB=H	OFF	

### 5.2 Timing Chart



Example of DC Brushless motor drive

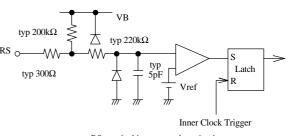
### 5.3 Overcurrent Limiting Operation

This IC detects overcurrent by outside resistance Rs.

When Rs input voltage exceeds inner reference voltage

Vref(0.5V typical), this IC turns off the bottom output. After overcurrent detection, a reset operation is done
at each inner clock signal period.

In case of not using this function, please connect Rs terminal to GL terminal.



RS terminal inner equvalent circuit

### 6. Standard Application

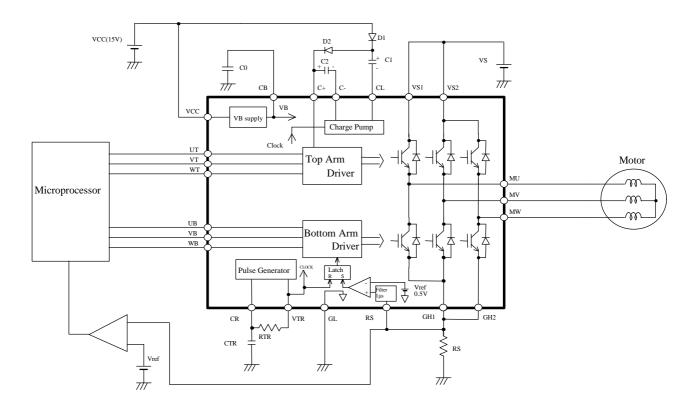
Component	Recommended Value	Usage	Remark
C0	More than 0.22 uF	for inner power supply(VB).	stress voltage is VB
C1,C2	1.0 uF +/- 20%	for charge pump	stress voltage is VCC
D1,D2	Hitachi DFG1C6(Glass mold type), DFM1F6 (Resin mold type) or considerable parts	For charge pump	600V/1.0A trr ≤ 100ns
CTR	1800 pF +/- 5%	for clock	Note 1.
RTR	22 k-ohm +/- 5%	for clock	Note 1.

Note 1. Clock frequency is determined approximately by next equation.

Floating capacitance of PCB must be considered.

At Recommended Value of CR, the error factor of IC is about 10%.

fclock = -1 / 
$$(2C*R*Ln(1-3.5/5.5))$$
 ; Ln is natural logarithm = 0.494 /  $(C*R)$  (Hz)



#### 7. Terminal

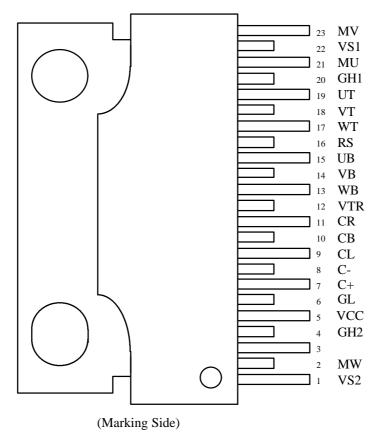
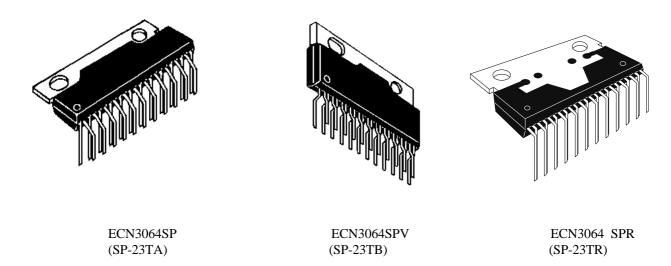


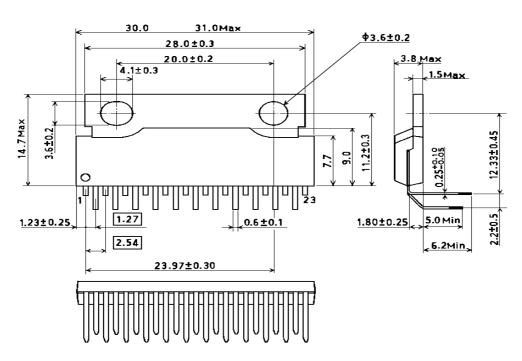
Fig.2 Pin Assignment

### 8. Package Outline

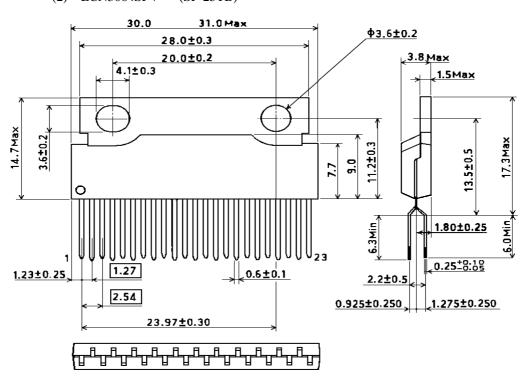


- 9. Package Dimensions
  - (1) ECN3064SP (SP-23TA)

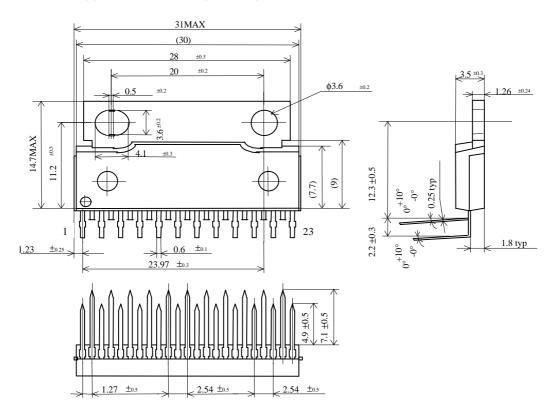
(Unit:mm)



(2) ECN3064SPV (SP-23TB)



### (3) ECN3064SPR (SP-23TR)



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